

DESCRIPTION

The 2301H uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

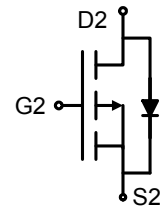
●

V_{DSS}	$R_{DS(ON)}$ @ -4.5V(Typ)	$R_{DS(ON)}$ @ -10V(Typ)	I_D
-30V	105m Ω	65m Ω	-2 A

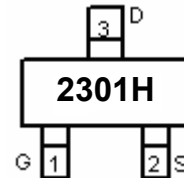
- High Power and current handing capability
- RoHS Compliant
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT-23

Ordering Information

Part Number	Marking	Case	Packaging
2301H	2301H	SOT-23	3000pcs/Reel

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	-2	A
Drain Current -Pulsed (Note 1)	I_{DM}	-10	A
Maximum Power Dissipation	P_D	1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	125	°C/W
--	-----------------	-----	------

Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20	-24	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$	-	-	-1	μA

Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-0.4	-1.6	-2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-2A	-	105	130	mΩ
		V _{GS} =-10V, I _D =-3A	-	65	125	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V,I _D =-2.8A	-	9.5	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-10V,V _{GS} =0V, F=1.0MHz	-	405	-	PF
Output Capacitance	C _{oss}		-	75	-	PF
Reverse Transfer Capacitance	C _{rss}		-	55	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-10V,I _D =-1A V _{GS} =-4.5V,R _{GEN} =10Ω	-	11	-	nS
Turn-on Rise Time	t _r		-	35	-	nS
Turn-Off Delay Time	t _{d(off)}		-	30	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =-10V,I _D =-3A, V _{GS} =-2.5V	-	3.3	12	nC
Gate-Source Charge	Q _{gs}		-	0.7	-	nC
Gate-Drain Charge	Q _{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =1.3A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-1.3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

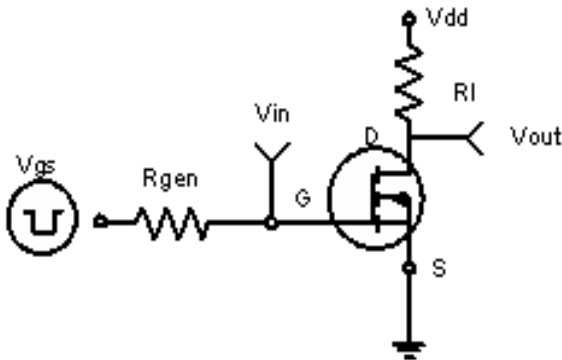


Figure 1: Switching Test Circuit

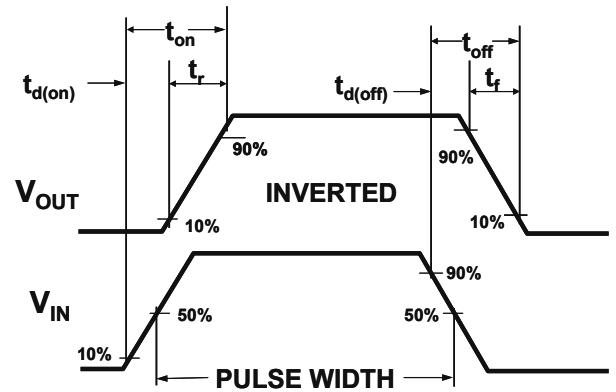


Figure 2: Switching Waveforms

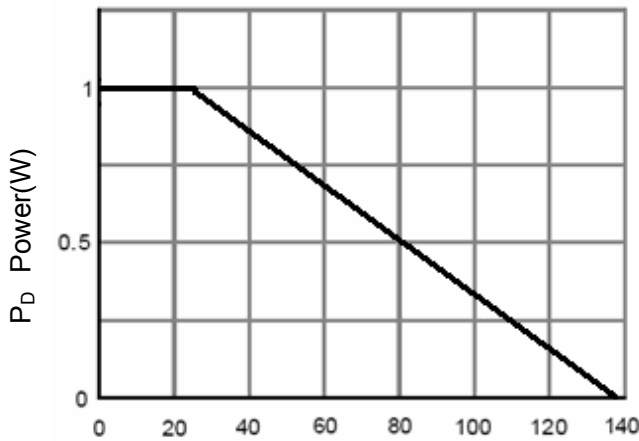


Figure 3 Power Dissipation

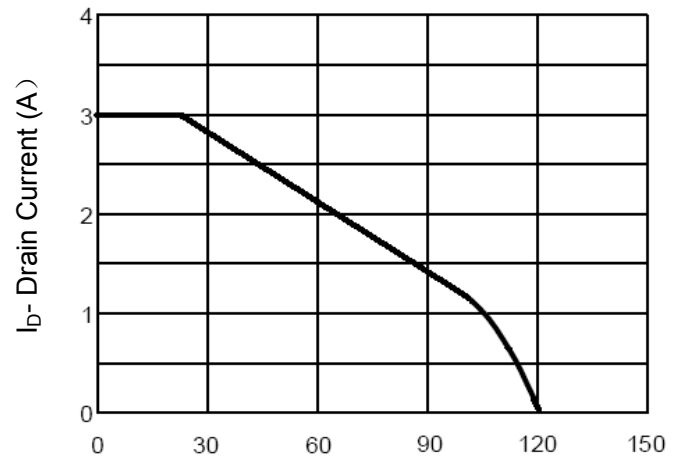


Figure 4 Drain Current

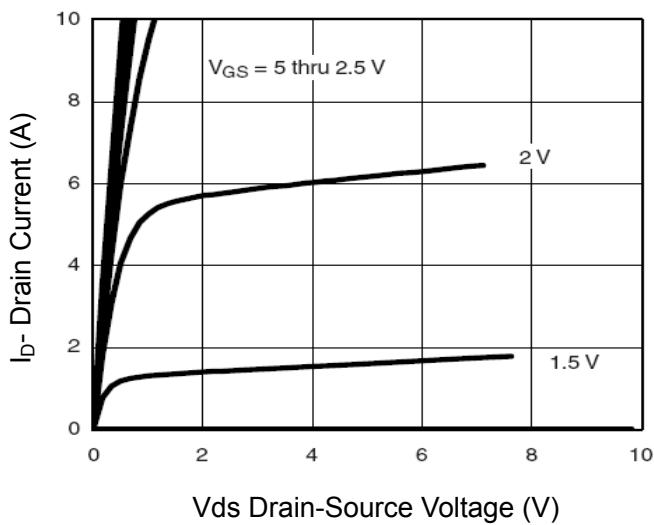


Figure 5 Output CHARACTERISTICS

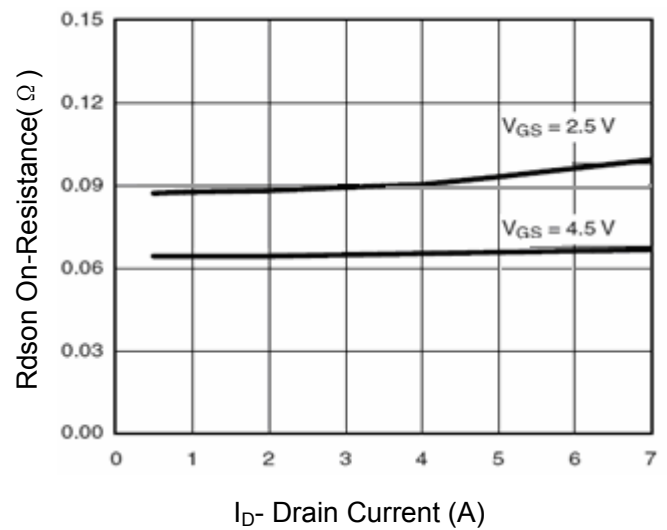


Figure 6 Drain-Source On-Resistance

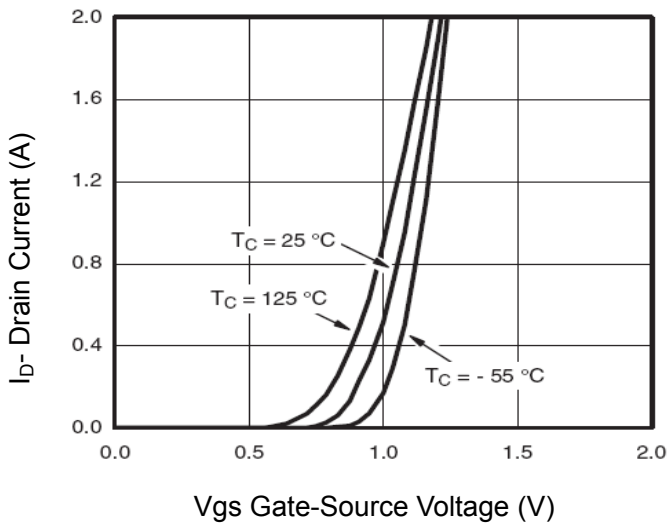


Figure 7 Transfer Characteristics

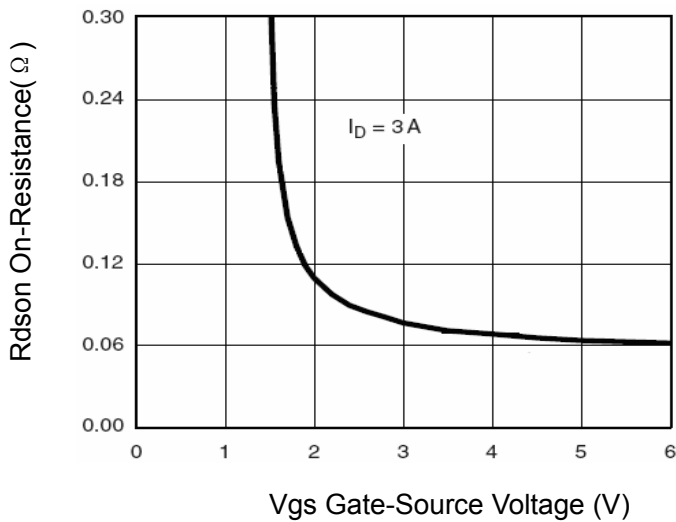


Figure 9 $R_{DS(on)}$ vs V_{GS}

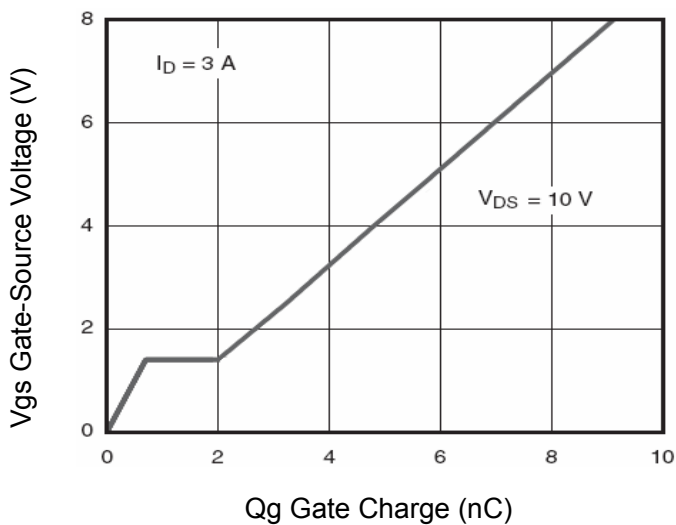


Figure 11 Gate Charge

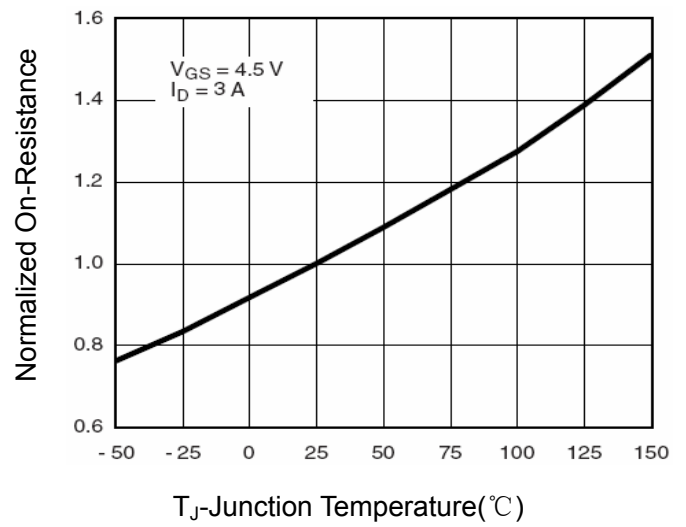


Figure 8 Drain-Source On-Resistance

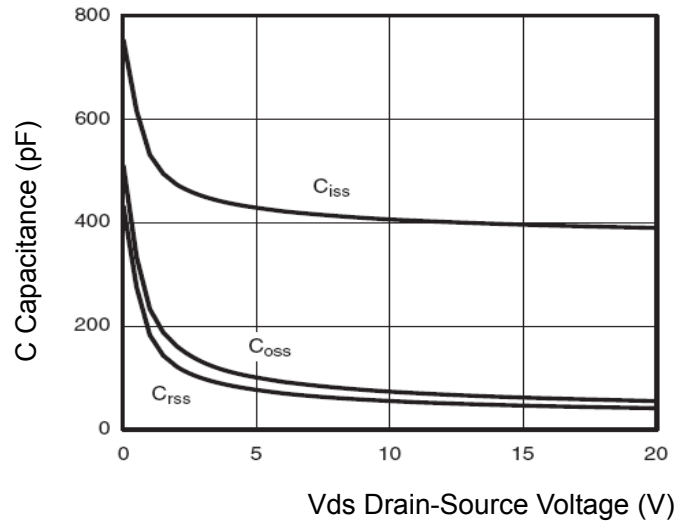


Figure 10 Capacitance vs V_{DS}

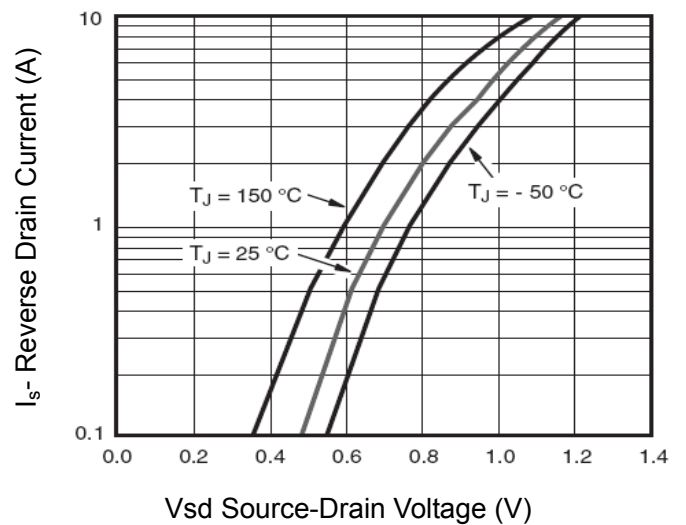


Figure 12 Source- Drain Diode Forward

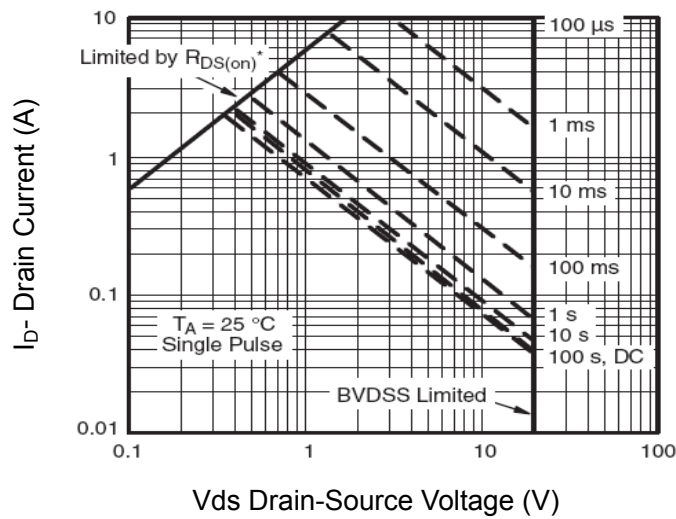


Figure 13 Safe Operation Area

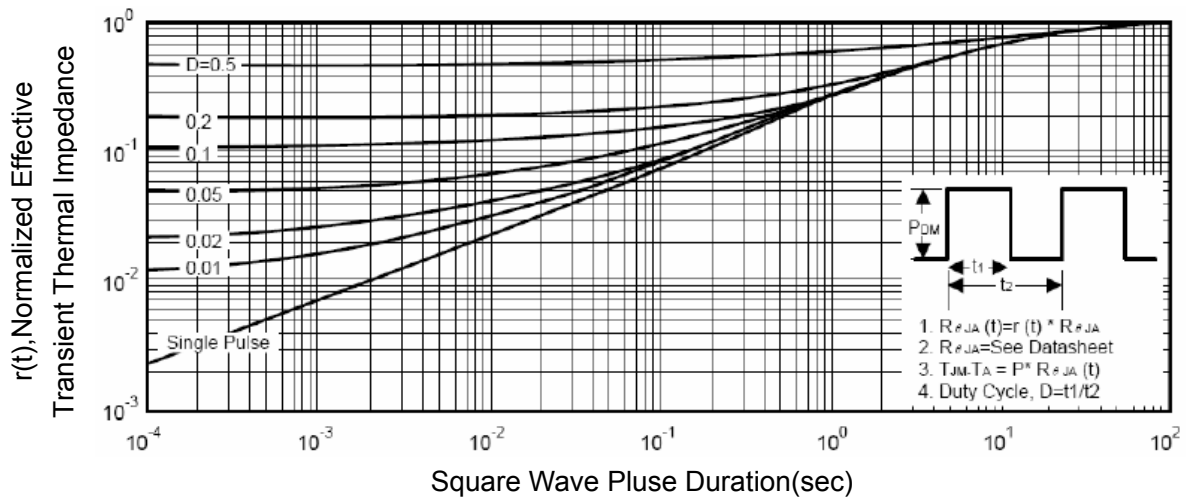
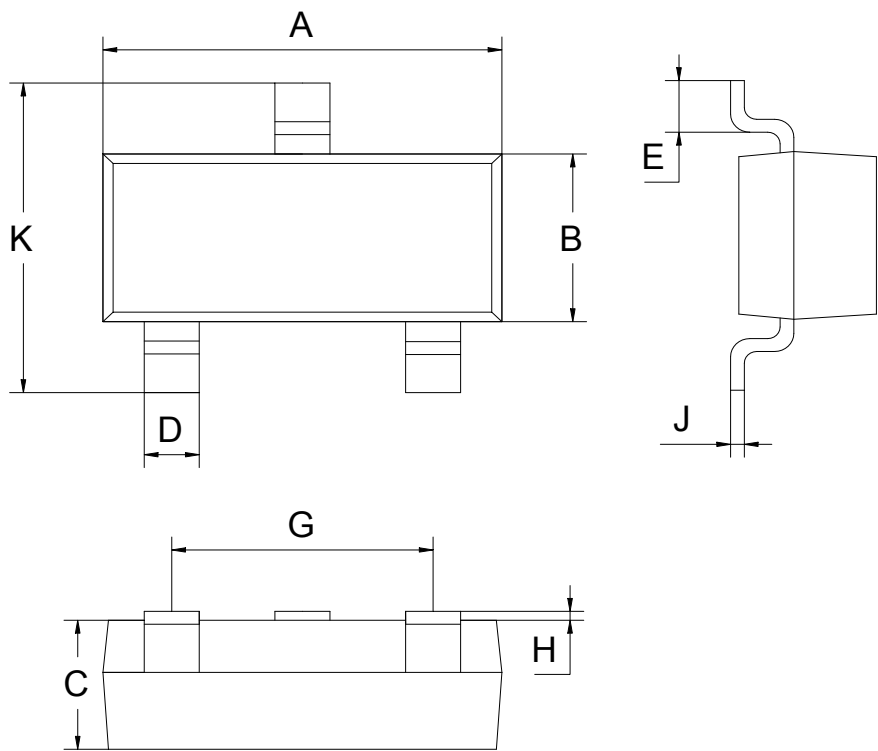


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package information



SOT-23			
Dim	MIN	NOM	MAX
A	2.80	2.90	3.00
B	1.20	1.30	1.40
C	0.90	1.00	1.10
D	0.39	0.40	0.45
E	0.20MIN		
G	1.90REF		
H	0.00	-	0.10
J	0.05	0.10	0.15
K	2.30	2.40	2.50
All Dimensions in mm			